CRMLTL2N7006K

N-Channel 60V, 4.9Ω Typ. Power MOSFET

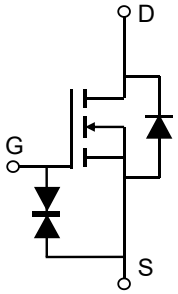
Description

Features

- 60V, 0.18A

  $R_{DS(ON)}$ Typ = 4.9Ω @ V_{GS} = 10V

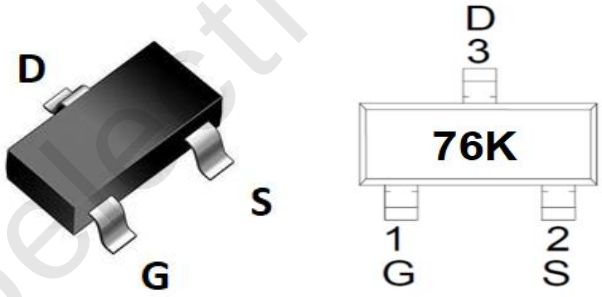
  $R_{DS(ON)}$ Typ = 5.5Ω @ V_{GS} = 4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free
- ESD Protected: 2KV



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMLTL2N7006K	76K	SOT-23	TAPING	7"	3000	120000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		60	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_A = 25°C	0.18	A
		T_A = 100°C	0.108	A
I_{DM}	Pulsed Drain Current [1]		0.72	A
P_D	Power Dissipation	T_A = 25°C	0.33	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient[2]		380	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±10	μA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1	1.5	2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 0.1A	-	4.9	5.9	Ω
		V_{GS} = 4.5V, I_D = 0.1A	-	5.5	6.6	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz	-	14	-	pF
C_{oss}	Output Capacitance		-	2	-	pF
C_{rss}	Reverse Transfer Capacitance		-	0.8	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 30V, I_D = 0.1A	-	1	-	nC
Q_{gs}	Gate Source Charge		-	0.2	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	0.4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 30V I_D= 0.1A, R_{GEN} = 6Ω	-	2.9	-	ns
t_r	Turn-On Rise Time		-	2.8	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	7	-	ns
t_f	Turn-Off Fall Time		-	6.5	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	0.18	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	0.72	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 0.1A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 0.1A, di/dt = 100A/us	-	11	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	3	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

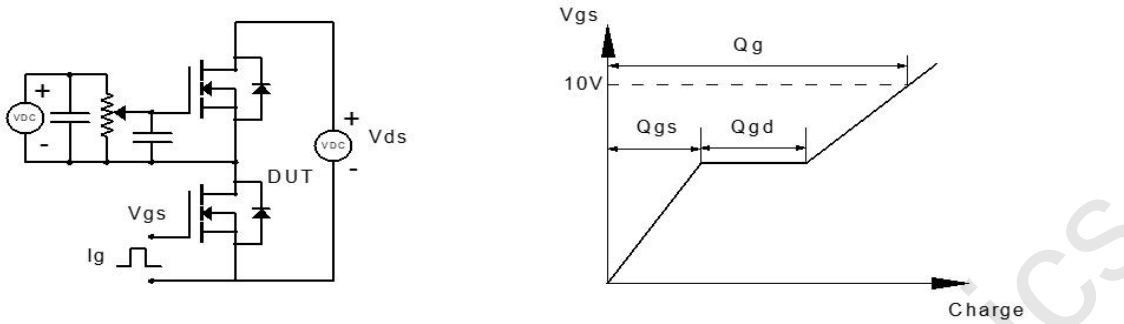


Figure 1: Gate Charge Test Circuit & Waveform

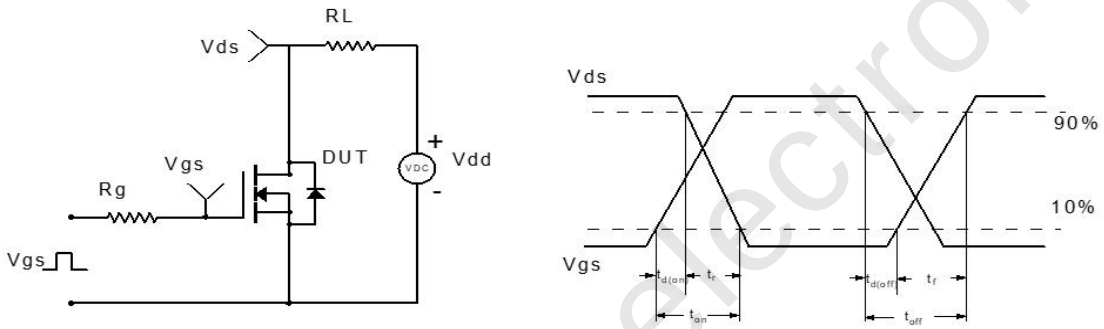


Figure 2: Resistive Switching Test Circuit & Waveform

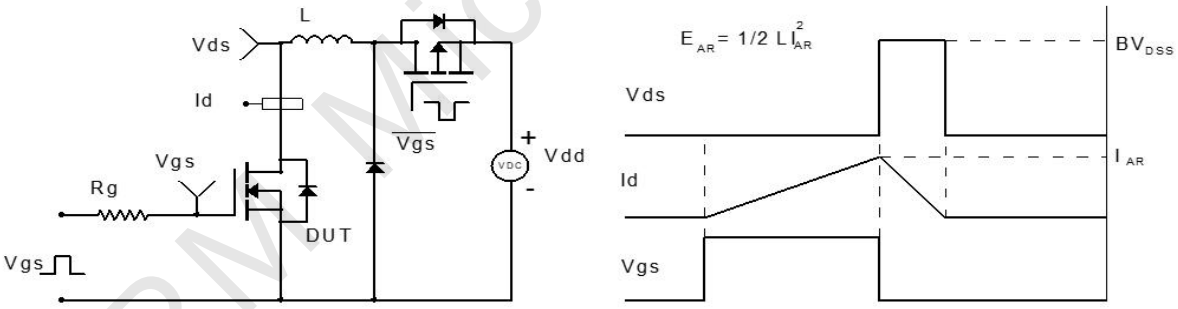


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

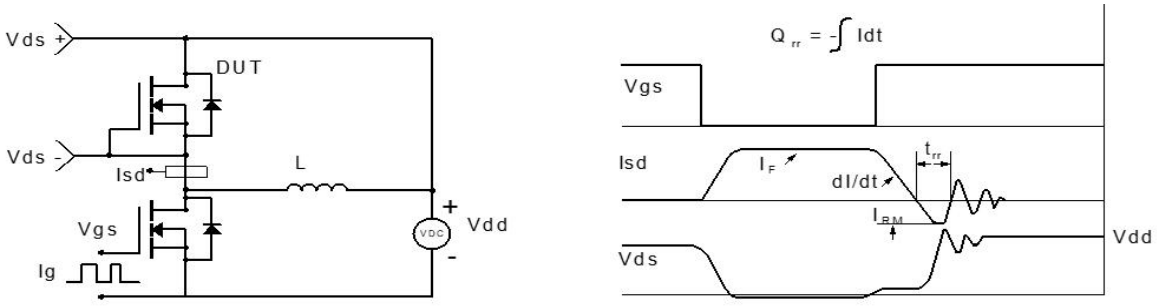
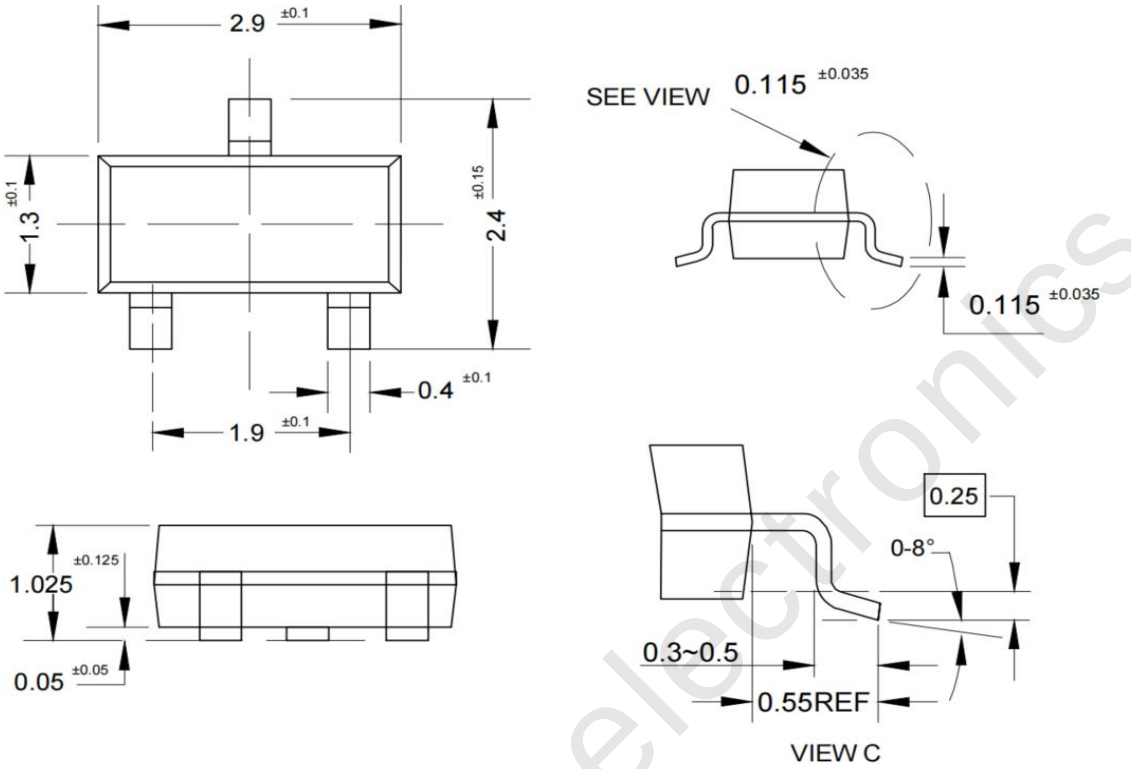


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23)



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